

230 — (Relaxed

SiGe, 220

218

Strained-Si

channel layer, 222

-4

process etches; Ge concentration greater than virtual buffer concentration if

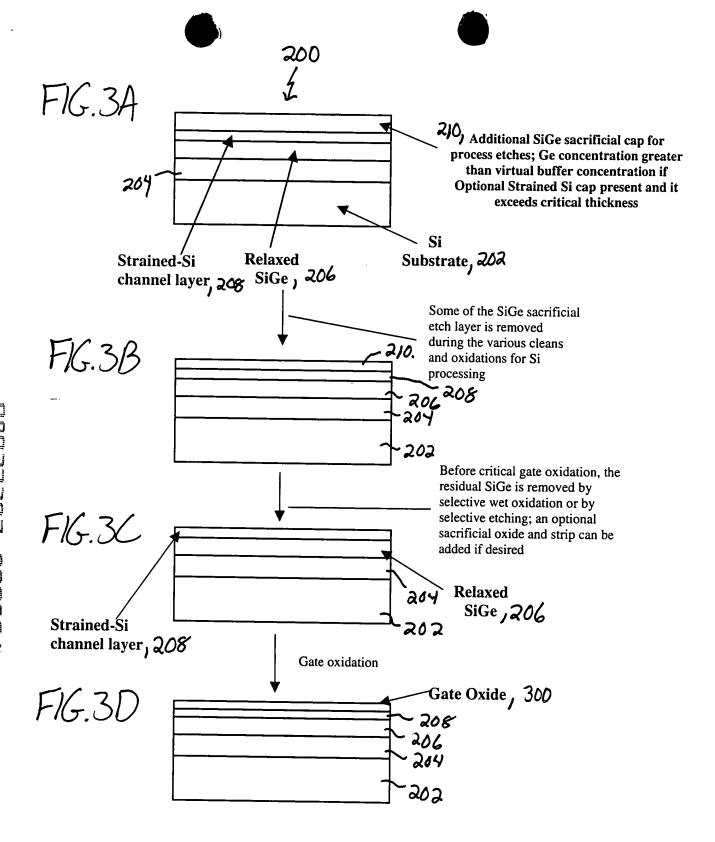
Optional Strained Si cap present and it exceeds critical thickness

Strained-Si

for gate-oxide, 224

Si

Substrate



214

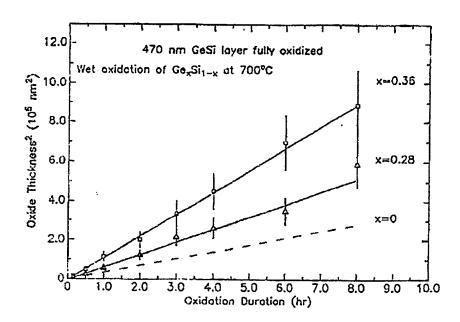


FIG.5

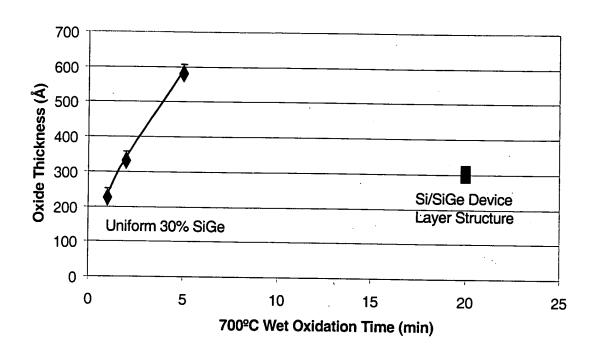


FIG. 6

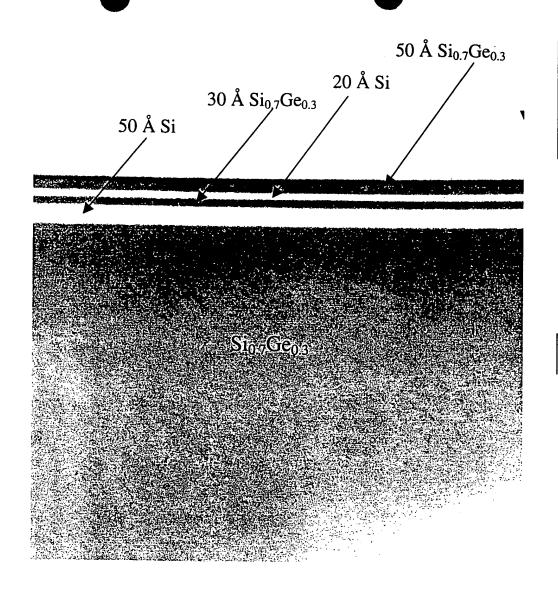


FIG.7

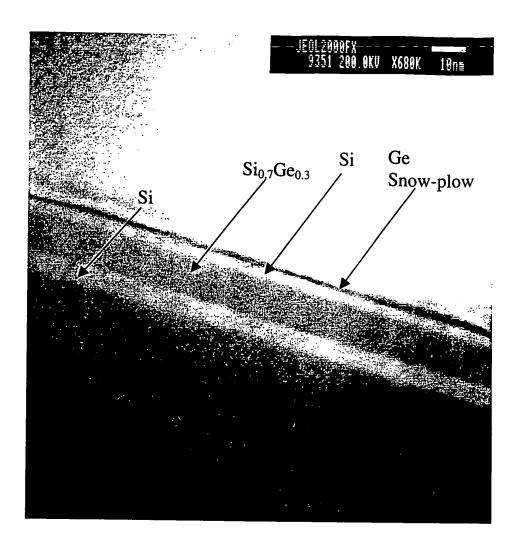
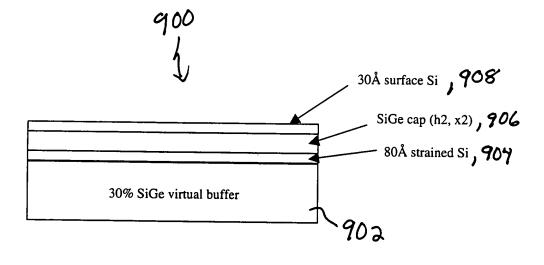


FIG. 8



F1G. 9

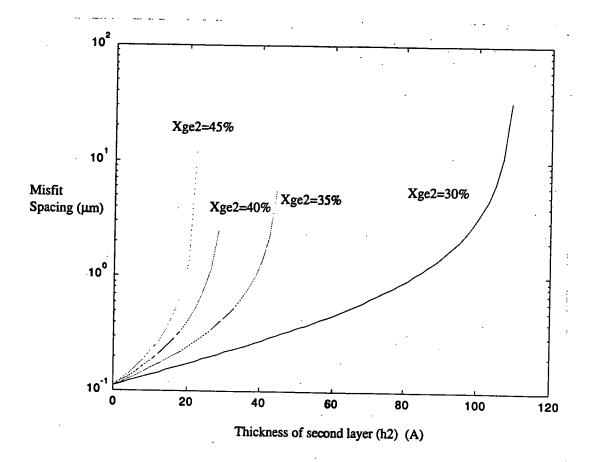


FIG. 10